

V _{CES}	650V
Ι _{C(100°C)}	20A
V _{CE(sat) (Typ.)}	1.6V
P _D	144W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating ; RoHS Compliant

Applications

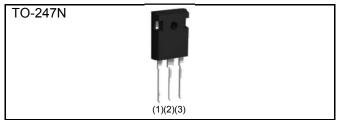
PFC

UPS

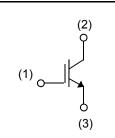
Power Conditioner

IH

Outline



Inner Circuit





Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	450
	Packing code	C11
	Marking	RGTH40TS65

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

			7	
Paramet	Symbol	Value	Unit	
Collector - Emitter Voltage	V _{CES}	650	V	
Gate - Emitter Voltage	V _{GES}	±30	V	
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	۱ _C	40	А
Collector Current	T _C = 100°C	Ι _C	20	А
Pulsed Collector Current	I _{CP} *1	80	А	
Power Dissinction	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	144	W
Power Dissipation	T _C = 100°C	P _D	72	W
Operating Junction Temperat	Tj	-40 to +175	°C	
Storage Temperature	T _{stg}	–55 to +175	°C	

*1 Pulse width limited by T_{imax.}

Datasheet

Thermal Resistance

Parameter	Symbol	Values			Unit
Faranielei		Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	1.04	°C/W

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	bol Conditions		Values		
Faranielei	Symbol Conditions -		Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	I _C = 10μΑ, V _{GE} = 0V	650	-	-	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	-	-	10	μA
Gate - Emitter Leakage Current	I _{GES}	V _{GE} = ±30V, V _{CE} = 0V	-	-	±200	nA
Gate - Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 5V, I _C = 13.3mA	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	I _C = 20A, V _{GE} = 15V T _j = 25°C T _j = 175°C	-	1.6 2.1	2.1 -	V



•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deremeter	Symbol	Conditiono	Values			Linit
Parameter	Symbol	Conditions	Min. Typ.		Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1060	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	47	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	18	-	
Total Gate Charge	Qg	V _{CE} = 300V	-	40	-	
Gate - Emitter Charge	Q _{ge}	I _C = 20A	-	9	-	nC
Gate - Collector Charge	Q _{gc}	V _{GE} = 15V	-	15	-	
Turn - on Delay Time	t _{d(on)}	I _C = 20A, V _{CC} = 400V	-	22	-	
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	25	-	20
Turn - off Delay Time	t _{d(off)}	T _j = 25°C	-	73	-	ns
Fall Time	t _f	Inductive Load	-	48	-	
Turn - on Delay Time	t _{d(on)}	I _C = 20A, V _{CC} = 400V	-	22	-	
Rise Time	t _r	V _{GE} = 15V, R _G = 10Ω	-	25	-	20
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	83	-	ns
Fall Time	t _f	Inductive Load	-	58	-	
		I _C = 80A, V _{CC} = 520V		-	-	
Reverse Bias Safe Operating Area RE		V _P = 650V, V _{GE} = 15V	FULL SQUARE		-	
		R _G = 60Ω, T _j = 175°C				



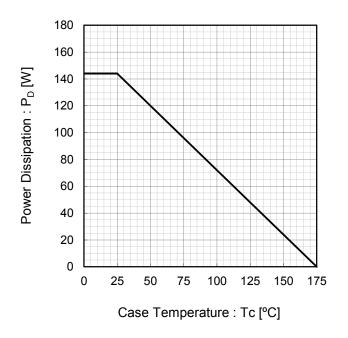


Fig.1 Power Dissipation vs. Case Temperature

Fig.2 Collector Current vs. Case Temperature

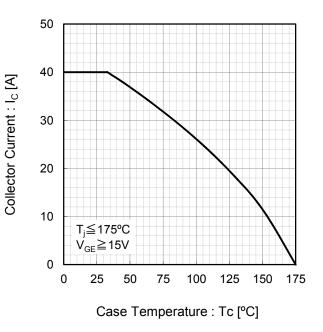
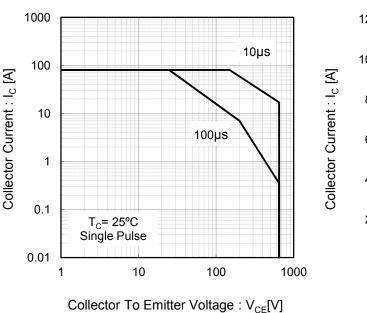
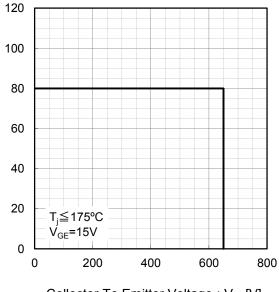


Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area





Collector To Emitter Voltage : $V_{CE}[V]$

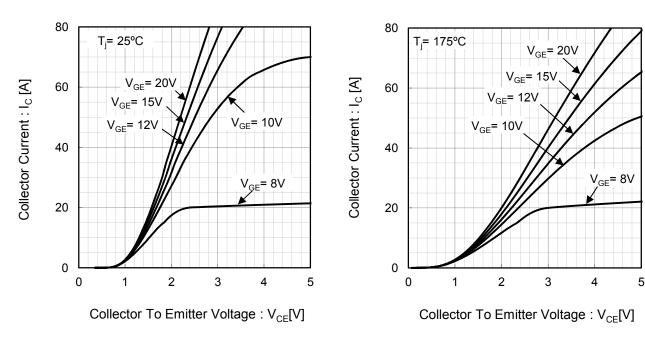


Fig.5 Typical Output Characteristics

Fig.6 Typical Output Characteristics

Fig.7 Typical Transfer Characteristics

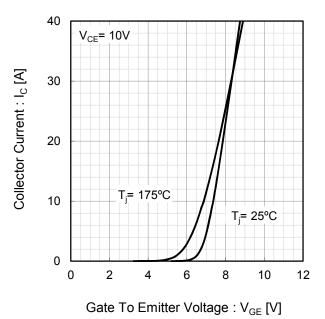
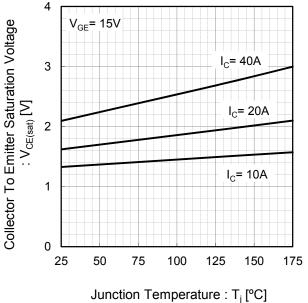


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



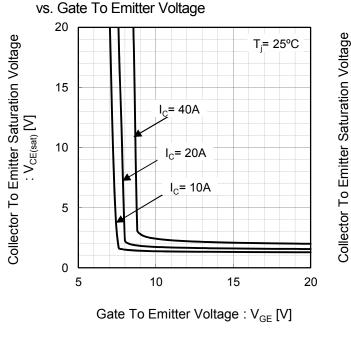
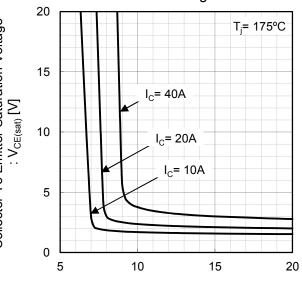


Fig.9 Typical Collector To Emitter Saturation Voltage

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V_{GE} [V]

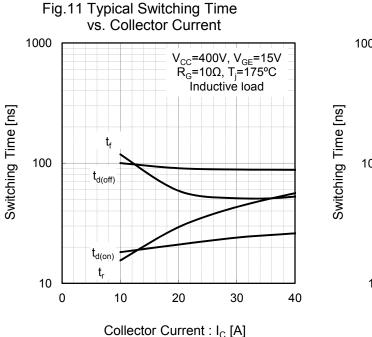
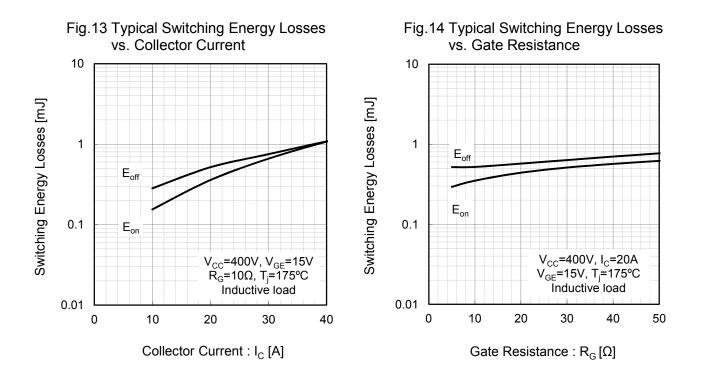


Fig.12 Typical Switching Time vs. Gate Resistance 1000 V_{CC}=400V, I_C=20A V_{GE}=15V, T_j=175°C Inductive load 100 t_{d(off)} t_f t_{d(on)} 10 10 20 30 40 50 0 Gate Resistance : $R_G[\Omega]$



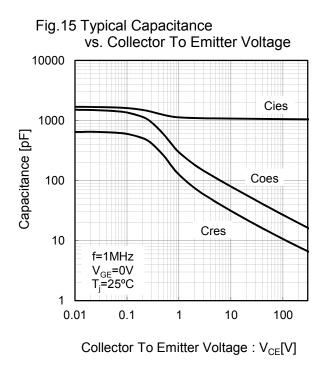
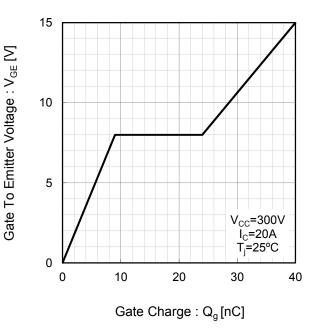


Fig.16 Typical Gate Charge



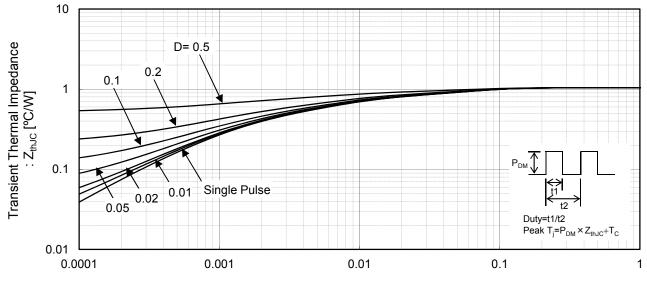


Fig.17 IGBT Transient Thermal Impedance

Pulse Width : t1[s]



●Inductive Load Switching Circuit and Waveform

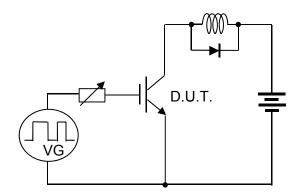
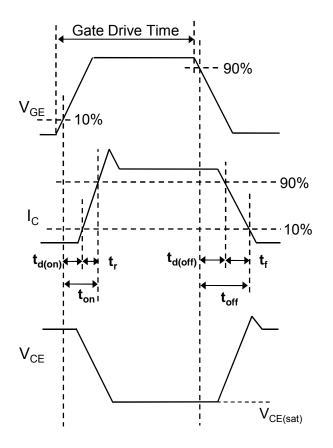


Fig.18 Inductive Load Circuit







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RGTH40TS65 - Web Page

Distribution Inventory

Part Number	RGTH40TS65
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	450
Packing Type	Bulk
Constitution Materials List	inquiry
RoHS	Yes



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